

Contents

1. Introduction	1
1.1 Historical Remarks	1
1.2 Surface Space-Charge and Surface States: Some Preliminary Remarks	13
2. Surface Space-Charge Region in Thermal Equilibrium	21
2.1 Solutions of Poisson's Equation.....	21
2.2 Surface Space-Charge	25
2.3 Shape of Surface Barriers	27
2.4 Comparison of Space-Charge Layers at Semiconductor and Metal Surfaces	28
2.5 Quantum Size-Effects in Space-Charge Layers	28
3. Surface States	33
3.1 Virtual Gap States of the Complex Band Structure	33
3.2 Intrinsic Surface States: Nearly Free Electron Model	36
3.3 Intrinsic Surface States: Tight-Binding Approximation	44
3.4 Dangling Bonds	47
3.5 Adatom-Induced Surface States: Tight-Binding Approach	51
3.6 Adatom-Induced Surface Dipoles: Electronegativity Concept .	53
3.7 Adatom-Induced Surface States and Dipoles: ViGS Model ...	56
4. Occupation of Surface States and Surface Band-Bending in Thermal Equilibrium	59
5. Surface Space-Charge Region in Non-Equilibrium	67
5.1 Surface Photovoltage.....	67
5.2 Dember Effect	73
5.3 Surface Transport	74
5.3.1 Surface Excess of Carriers	74
5.3.2 Surface Conductance	76
5.3.3 Surface Mobility	76
5.3.4 Field Effect of Surface Conductance	78

- 6. Interface States** 81
 - 6.1 Metal–Semiconductor Contacts: Metal–Induced Gap States .. 81
 - 6.2 MIGS-and-Electronegativity Model
of Metal–Semiconductor Contacts 86
 - 6.3 Slope Parameters of Barrier Heights in Schottky Contacts . . . 91
 - 6.4 Defects at Metal–Semiconductor Interfaces 93
 - 6.5 Band Lineup in Semiconductor Heterostructures:
IFIGS-and-Electronegativity Model 96
 - 6.6 Band Lineup at Semiconductor Heterostructures:
Tight-Binding Approach 98
 - 6.7 Historical Notes 100

- 7. Cleaved {110} Surfaces of III-V
and II-VI Compound Semiconductors** 105
 - 7.1 Ionicity and Core-Level Spectroscopy
of Compound Semiconductors 105
 - 7.1.1 Layer Model of Photoemitted Electrons 105
 - 7.1.2 Charge Transfer in the Bulk
of Compound Semiconductors 109
 - 7.2 Surface Core-Level Shifts 112
 - 7.3 Geometrical Surface Structure 114
 - 7.4 Surface Phonons 122
 - 7.5 Electronic Surface States 128
 - 7.5.1 Intrinsic Versus Extrinsic Surface States 128
 - 7.5.2 Cleavage-Induced Surface States:
InAs(110) as an Example 131
 - 7.5.3 Intrinsic Surface States 133
 - 7.6 Temperature Dependence of the Ionization Energy 137
 - 7.7 Chemical Trends of the Ionization Energy 140

- 8. {100} Surfaces of III-V, II-VI,
and I-VII Compound Semiconductors
with Zincblende Structure** 145
 - 8.1 Reconstructions and Trends in Chemical Compositions 145
 - 8.2 Dimerization 150
 - 8.3 Missing Dimer Structures 153
 - 8.4 Dimerization, Occupation of Dangling Bonds,
and Electron Counting 161
 - 8.5 Intrinsic Surface Band Structure 166
 - 8.6 Fermi-Level Pinning by Extrinsic Surface States 167
 - 8.7 Ionization Energy 168

- 9. {100} Surfaces of Diamond, Silicon, Germanium,
and Cubic Silicon Carbide** 169
 - 9.1 Atomic Arrangement 169

9.2	Strain Effects on Si(001) Surfaces	175
9.3	Electronic Surface Properties	177
9.4	Surface Core-Level Shifts	181
9.5	Reversible $2 \times 1 \rightleftharpoons c(4 \times 2)$ Surface Phase Transition	183
9.6	β -SiC(001) Surfaces	186
10.	Diamond, Silicon, and Germanium	
	{111}-2×1 Surfaces	193
10.1	Cleaved Silicon and Germanium Surfaces	194
10.1.1	Early Models of (111)- 2×1 Reconstructions and Core-Level Shifts	194
10.1.2	Band Structure of Dangling-Bond Surface States: Experimental Data	197
10.1.3	Surface Band Gap	202
10.1.4	Tilted Chains	206
10.1.5	Band Structure of Dangling-Bond Surface States: Theoretical Results	213
10.2	Clean Diamond {111} Surfaces	213
10.2.1	Atomic Arrangement	213
10.2.2	Electronic Properties	215
10.3	Clean Diamond and Cleaved Silicon and Germanium {111} Surfaces in Comparison	217
11.	Si(111)-7×7 and Ge(111)-$c(2 \times 8)$ Surfaces	219
11.1	Preparation of Clean Si(111)- 7×7 and Ge(111)- $c(2 \times 8)$ Surfaces	219
11.2	Si(111)- 7×7 : Atomic Arrangement	221
11.2.1	Elements of the 7×7 Reconstruction on Si(111) Surfaces	221
11.2.2	Dimer-Adatom-Stacking Fault Model	225
11.3	Ge(111)- $c(2 \times 8)$: Atomic Arrangement	229
11.4	Electronic Structure of Si(111)- 7×7 and Ge(111)- $c(2 \times 8)$ Surfaces	232
11.4.1	Electronic Band Structure	232
11.4.2	Core-Level Spectroscopy	234
11.5	Energetics of Reconstructions on {111} Surfaces of Si and Ge: 7×7 Versus $c(2 \times 8)$	237
12.	Phase Transitions on Silicon and Germanium	
	{111} Surfaces	241
12.1	Si(111)- $7 \times 7 \rightleftharpoons "1 \times 1"$ and Ge(111)- $c(2 \times 8) \rightleftharpoons "1 \times 1"$ Phase Transitions	241
12.2	Ge(111)-" 1×1 " High-Temperature Phase Transition	246
12.3	Irreversible Conversion of 2×1 Reconstructions on Cleaved Si and Ge Surfaces	247

13. {111} Surfaces of Compounds with Zincblende Structure .	255
13.1 [111]-Oriented Surfaces	255
13.2 $\bar{1}\bar{1}\bar{1}$ -Oriented Surfaces	257
14. Monovalent Adatoms	263
14.1 Adsorption of Halogens	263
14.1.1 Dissociative Adsorption	263
14.1.2 Bond Lengths and Adsorption Sites	269
14.2 Adsorption of Hydrogen	272
14.2.1 Si(001):H-Surfaces	272
14.2.2 Si(111):H- $\delta(7 \times 7)$ Surfaces	275
14.2.3 Si(111)- and Ge(111):H- 1×1 Surfaces	276
14.3 Alkali and Silver Adatoms on Si{100} Surfaces	280
14.4 Monovalent Metal Adatoms on Si and Ge {111} Surfaces	283
14.4.1 Alkali Adatoms on Si(111)- 7×7 Surfaces	283
14.4.2 Si(111):Ag- and Ge(111):Ag- $(\sqrt{3} \times \sqrt{3})R30^\circ$ Structures	284
14.4.3 Si(111):Au- and Ge(111):Au- $(\sqrt{3} \times \sqrt{3})R30^\circ$ Structures	287
14.4.4 3×1 Reconstructions Induced by Alkali and Silver Adatoms on Si (111) Surfaces	288
14.5 Growth Kinetics of Metals on Cleaved GaAs(110) Surfaces	291
14.6 Adatom-Induced Surface Core-Level Shifts	300
14.7 Adatom-Induced Surface Dipoles	307
14.7.1 Mutual Interactions in Plane Arrays of Surface Dipoles	307
14.7.2 Surface Dipoles Induced by Alkali Adatoms	309
14.7.3 Hydrogen-Induced Surface Dipoles	311
14.8 Adatom-Induced Surface States	316
14.8.1 Cesium Adatoms on Cleaved Si Surfaces	316
14.8.2 Metal Adatoms on GaAs(110) Surfaces	317
14.8.3 Nonmetal Adatoms on GaAs(110) Surfaces	324
15. Group-III Adatoms on Silicon Surfaces	329
15.1 Si(111):III- $(\sqrt{3} \times \sqrt{3})R30^\circ$ Reconstructions	329
15.1.1 Al-, Ga-, and In-Induced $(\sqrt{3} \times \sqrt{3})R30^\circ$ Reconstructions	330
15.1.2 B-Induced $(\sqrt{3} \times \sqrt{3})R30^\circ$ Reconstruction	333
15.2 Reconstructions Induced by Group-III Adatoms on {100} Surfaces of Si and Ge	334
16. Group-V Adatoms	339
16.1 Si(111):As- 1×1 and Si(001):As- and Si(001):Sb- 2×1 Surfaces	339

16.2	Sb- and Bi-induced ($\sqrt{3} \times \sqrt{3}$)R30° Structures on Si and Ge(111) Surfaces	343
16.3	GaP-, GaAs-, and InP(110):Sb-1 × 1 Surfaces	347
16.4	III-V(110):Bi-1 × 1 Surfaces	350
17.	Oxidation of Silicon and III-V Compound	
	Semiconductors	353
17.1	Si(111) Surfaces	353
17.1.1	Precursor-Mediated Chemisorption on Si(111)-7 × 7 Surfaces	354
17.1.2	Oxygen-Induced Si(2 <i>p</i>) Core-Level Shifts	361
17.1.3	Field-Assisted Oxidation	364
17.2	III-V Compound Semiconductors	366
17.2.1	Oxidation Kinetics on GaAs(110) Surfaces	367
17.2.2	Photon-Stimulated Oxidation	371
17.2.3	Core-Level Spectroscopy: Growth Mode and Composition of Oxide Films	372
18.	Surface Passivation by Adsorbates and Surfactants	377
18.1	Surface Passivation by Hydrogen	377
18.2	Surfactant-Mediated Growth	381
19.	Semiconductor Interfaces	385
19.1	Metal–Semiconductor Contacts	386
19.1.1	Current Transport Across Metal–Semiconductor Contacts	386
19.1.2	Image-Force Effect	388
19.1.3	Determination of Barrier Heights: A Brief Comparison of Methods	389
19.1.4	Barrier Heights of Real Schottky Contacts	392
19.1.5	Laterally Inhomogeneous Schottky Contacts 1: Circular Patches	400
19.1.6	Laterally Inhomogeneous Schottky Contacts 2: BEEM	402
19.1.7	Laterally Inhomogeneous Schottky Contacts 3: <i>I/V</i> Characteristics	407
19.1.8	The MIGS-and-Electronegativity Concept: Experiment and Theory	411
19.1.9	Direct Observations of MIGS	418
19.1.10	Extrinsic Interface Dipoles 1: Interface Doping	420
19.1.11	Extrinsic Interface Dipoles 2: Metal/Si(111)-(7 × 7) ⁱ Contacts	424
19.1.12	Extrinsic Interface Dipoles 3: Epitaxial Silicide/Silicon Interfaces	427

19.1.13	Origin of Lateral Barrier-Height Inhomogeneities 1: Natural Nonuniformities	434
19.1.14	Origin of Lateral Barrier-Height Inhomogeneities 2: Extrinsic Nonuniformities	435
19.1.15	Slope Parameter	437
19.1.16	Schottky Contacts on Ternary III-V Alloys	439
19.1.17	Temperature and High-Pressure Effects	444
19.1.18	Ohmic Contacts	451
19.2	Semiconductor Heterostructures	455
19.2.1	Band-Structure Lineup	455
19.2.2	Interface Dipoles at Polar Interfaces	457
19.2.3	Lattice-Matched Ternary and Quaternary III-V Alloys	461
19.2.4	Pressure and Temperature Dependence of Valence-Band Offsets	467
19.2.5	Pseudomorphic Interfaces	468
19.2.6	Metamorphic Heterostructures	471
19.3	Layered Semiconductors	472
19.4	Insulator Interfaces	476
19.4.1	Metal–Insulator Contacts	476
19.4.2	Semiconductor–Insulator Interfaces	479
Appendix		483
References		487
Index of Reconstructions and Adsorbates		535
Subject Index		539